IR Chip--ORT114IRA-L

1. Scope：

- This specification applies to GaAlAs/GaAlAs infrared emitting diode chips

2. Structure：

- Mesa Type：rough surface.
- Electrodes：
  P（Anode）Side： gold alloy.
  N（Cathode）Side：gold alloy.

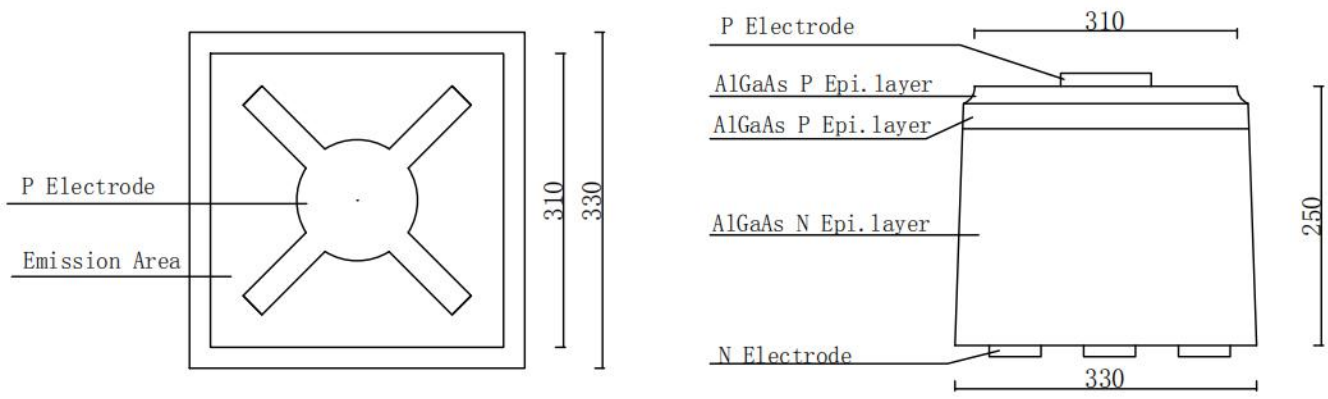
3. Size：

- Top Size：310μm×310μm ±30μm； Bottom Size：330μm×330μm ±30μm
- Chip Height：250μm±15μm
- Pad Size：120μm±10μm
- Pattern Drawing：fig.1.

4. Electro-Optical Characteristics：

（Ta=+25℃）

Parameter	Symbol	Unit	Min	Typ	Max	Test Condition
Forward voltage	V_F	V		1.4	1.7	I_F=300mA
Forward voltage	V_F	V	1.0	1.25	1.3	I_F=20mA
Reverse voltage	V_R	V	5			I_R=10μA
Peak wavelength	WLP	nm	930	940	950	I_F=20mA
Radiated output Power	P_O	mw	1.7		3	I_F=20mA



unit： μm

fig.1

5. Packing and Labeling：

- Packing：Sheet Type
- Each pellet is mounted on an adhesive sheet with wire-bonded electrode side up.
- Labeling：Each lot has a label sheet、writing Type、Lot No、Pcs、Avg P_O、V_F 、Wlp and

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quantity of good chips.

6. Application Notes：

- All data are measured by Orient’s tester on bare chips within 98% of the nominal value.
- Measurement error for dominant wavelength and peak wavelength is ±5nm

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